

SiC Schottky Barrier Diode

V_R	650V
I _F	8A
Q_{C}	21nC

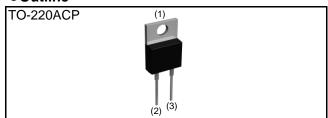
Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible
- 4) High surge current capability

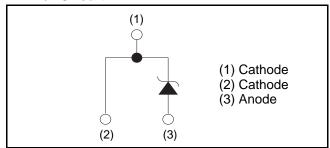
Construction

Silicon carbide epitaxial planar type

●Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	50
	Packing code	C9
	Marking	SCS308AH

● Absolute Maximum Ratings (T_i = 25°C)

Parameter		Symbol	Value	Unit
Reverse voltage (re	epetitive peak)	V_{RM}	650	V
Reverse voltage (D	C)	V_R	650	V
Continuous forward	l current (T _c =135°C)	I _F	8	А
Surge non-	PW=10ms sinusoidal, T _j =25°C		67	А
repetitive forward	PW=10ms sinusoidal, T _j =150°C	I_{FSM}	57	A
current	PW=10μs square, T _j =25°C		250	А
Repetitive peak forward current		I _{FRM}	36 * ¹	А
1≦PW≦10ms, T _j =25°C		.∫ i²dt	22	A ² s
i ² t value 1≦PW≦10ms, T _j =150°C		J I-at	16	A ² s
Total power disspation		P_{D}	57 *²	W
Junction temperature		Tj	175	°C
Range of storage temperature		T_{stg}	-55 to +175	°C

^{*1} T_c=100°C, T_i=150°C, Duty cycle=10% *2 T_c=25°C

●Electrical characteristics (T_j = 25°C)

Parameter Symbol Conditions	Cumbal	Conditions	Values			Unit
	Min.	Тур.	Max.			
DC blocking voltage	V_{DC}	I _R =40μA	650	-	-	V
	V _F	I _F =8A,T _j =25°C	-	1.35	1.50	V
Forward voltage		I _F =8A,T _j =150°C	-	1.44	1.71	V
		I _F =8A,T _j =175°C	-	1.50	-	V
Reverse current	I _R	V _R =650V,T _j =25°C	-	0.024	40	μΑ
		V _R =650V,T _j =150°C	-	1.6	160	μΑ
		V _R =650V,T _j =175°C	-	4.8	-	μΑ
Total capacitance	С	V _R =1V,f=1MHz	-	400	-	pF
		V _R =650V,f=1MHz	-	36	-	pF
Total capacitive charge	Q_{C}	V _R =400V,di/dt=350A/μs	-	21	-	nC
Switching time	t _C	V _R =400V,di/dt=350A/μs	-	15	-	ns
Non-repetetive Avaranche Energy	E _{ava}	L=1mH	-	110	1	mJ

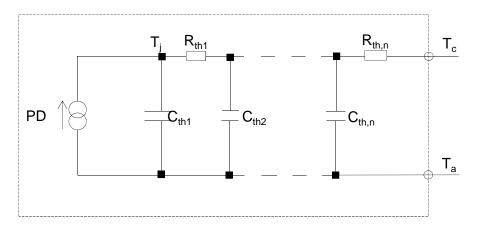
●Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
Thermal resistance	R _{th(j-c)}	-	-	1.8	2.6	°C/W

●Typical Transient Thermal Characteristics

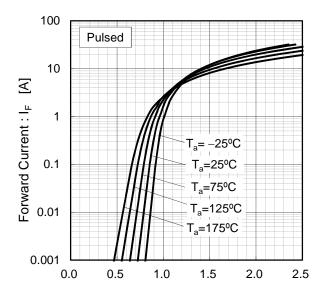
Symbol	Value	Unit
R _{th1}	1.89E-02	
R _{th2}	1.81E-01	K/W
R _{th3}	1.55E+00	

Symbol	Value	Unit
C_{th1}	1.95E-04	
C_{th2}	8.01E-04	Ws/K
C_{th3}	1.82E-03	



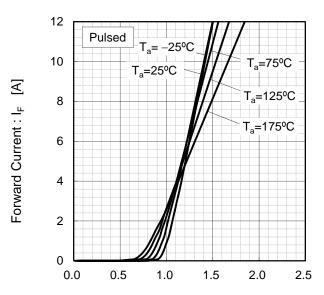
•Electrical characteristic curves

Fig.1 V_F - I_F Characteristics



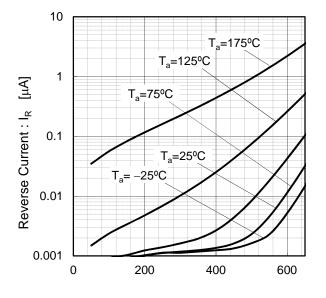
Forward Voltage : V_F [V]

Fig.2 V_F - I_F Characteristics



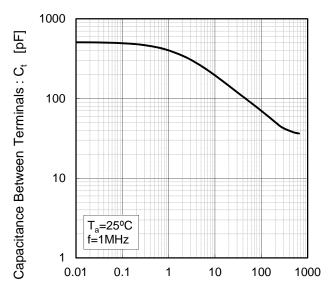
Forward Voltage : V_F [V]

Fig.3 V_R - I_R Characteristics



Reverse Voltage : V_R [V]

Fig.4 V_R-C_t Characteristics



Reverse Voltage : V_R [V]

•Electrical characteristic curves

Fig.5 Typical Transient Thermal Resistance vs. Pulse Width

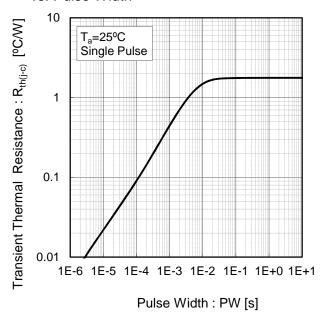
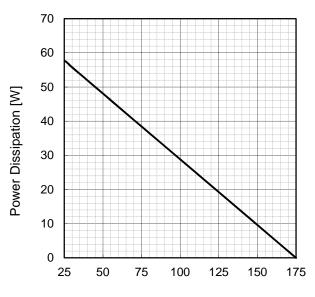
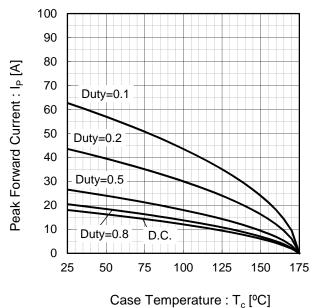


Fig.6 Power Dissipation



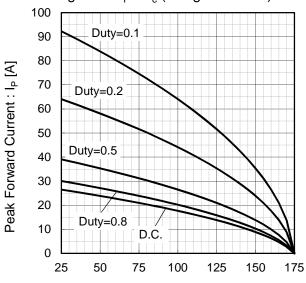
Case Temperature : T_c [°C]

Fig.7*3 Maximum peak forward current derating curve $I_P - T_c$



*3 Based on max Vf, max $R_{\text{th(j-c)}}$ Valid for switching of above 10kHz, excluding D.C. curve.

Fig.8*4 Typical peak forward current derating curve $I_P - T_c$ (Not guaranteed)



Case Temperature : T_c [°C]

 $^{\star}4$ Based on typ Vf, typ $R_{th(j\text{-}c)}$ Typical value, not guaranteed Valid for switching of above 10kHz, excluding D.C. curve

•Electrical characteristic curves

Fig.9 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)

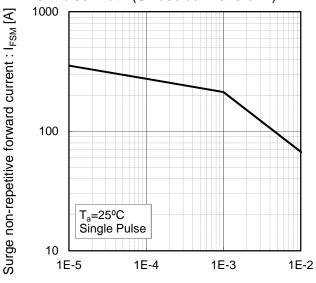
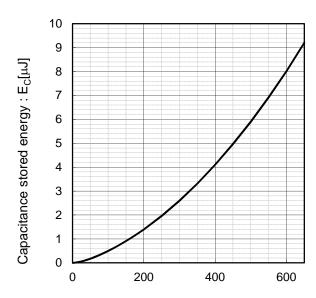


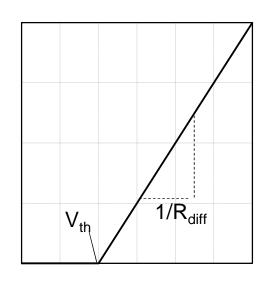
Fig.10 Typical capacitance store energy



Reverse Voltage: V_R [V]

Fig.11 Equivalent forward current curve

Pulse Width: PW [s]



Forward Voltage : V_F

$$V_F = V_{th} + R_{diff} I_F$$

$$\begin{aligned} &V_{th}\left(\:T_{j}\:\right) = a_{0} + a_{1}\:T_{j} \\ &R_{diff}\left(\:T_{j}\:\right) = b_{0} + b_{1}\:T_{j} + b_{2}\:T_{j}^{2} \end{aligned}$$

Symbol	Typical Value	Unit
a_0	9.66E-01	V
a ₁	- 1.10E-03	V/°C
b_0	4.40E-02	Ω
b ₁	9.33E-05	Ω/°C
b ₂	9.60E-07	Ω /°C ²

 $T_i \text{ in } {}^{\circ}\text{C}; -55 {}^{\circ}\text{C} < T_i < 175 {}^{\circ}\text{C}; I_F < 16\text{A}$

Forward Current: IF

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